

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

Please replace the paragraph beginning at page 13, line 3, with the following

amended paragraph:

As shown in Fig. 2, when the seed crystal substrate 1 is dipped in a melt 5 retained at the eutectic temperature, heat escapes by a rotating/vertical drive shaft 14 of the seed crystal substrate 1, thereby decreasing the temperature of the surface of the seed crystal substrate 1 to the temperature of crystallization. As a result, as shown in Fig. 1(B), a nitride 3 grown by graphoepitaxy is formed along the catalyst 2. As shown in Fig. 1(C), Ga-containing nitride single crystals 4 are grown ~~to provide entire coverage on the entire surface of the seed crystal substrate~~, thereby making single crystals of a Ga-containing nitride having a thickness of about 100 to 200 μm .